

Electronics project



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Circuit Schematics:

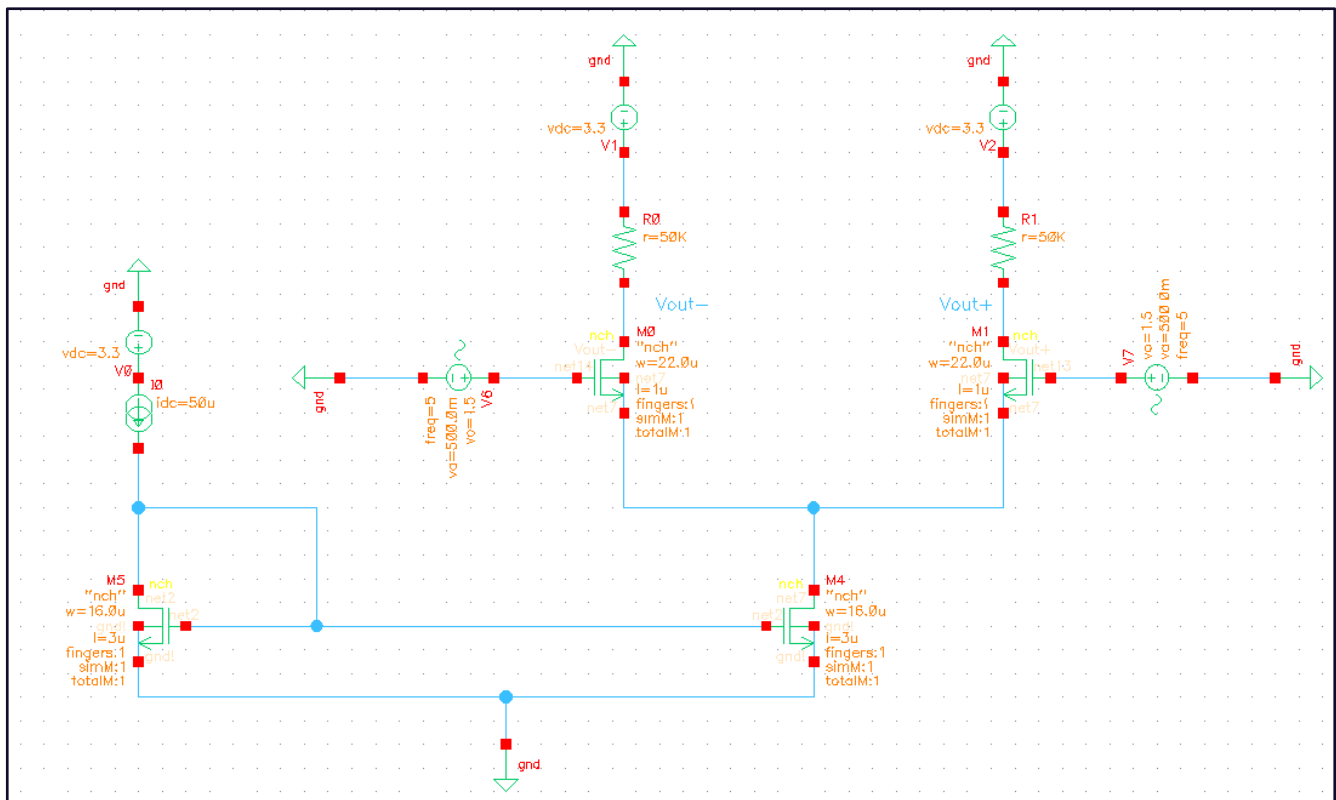


Figure 1: Problem 1 circuit

- a. Run DC with VCM=1.5V**
- i. Show the DC voltages of all points and validate it using hand calculations

hand analysis:

Due to symmetry in **Q1** and **Q2** , we can see this is a current mirror circuit so:

$$I_{DS3} = I_{DS2} = 50 \mu A$$

Now we can see that **Q2** works as a current source to the differential pair **Q3** and **Q4** which are clearly symmetric so the current will be divided equally in each transistor

$$I_{DS0} = I_{DS1} = 25 \mu A$$

$$\begin{aligned} V_{out-} &= V_{out} + \\ &= V_{DD} - R \times i_{ds1} = 3.3 - 50 \times 10^3 \times 25 \times 10^{-6} = 2.05 V \end{aligned}$$

$$V_{GS0} = V_{GS M1} = 342.3 mV \text{ from simulation dc analysis}$$

$$V_{SO,1} = V_{CM} - V_{GS} = 1.5 - 342.3 \times 10^{-3} = 1.1577 V$$

Assume all transistors are in saturation mode :

$$V_{SO,1} = V_{CM} - V_{GS} = 1.5 - 0.3423 = 1.1577 V$$

Check saturation:

For **M4**:

$$\begin{aligned} V_{DS M4} &> V_{GS M4} - V_{TH} \\ V_{DS M4} &= V_{S M0,M1} = 1.158 V \\ V_{GS M4} - V_{TH} &= 498.8 - 323.8 = 175 mV \end{aligned}$$

✓ **Correct Assumption**

For **M0** and **M1**:

$$\begin{aligned} V_{DS M0,M1} &> V_{GS M0,M1} - V_{TH M0,M1} \\ V_{DS M0,M1} &= 2.05 - 1.158 = 0.892 V \\ V_{GS M0,M1} - V_{TH M0,M1} &= 0.3423 - 0.3359 = 6.4 mV \end{aligned}$$

✓ **Correct Assumption**

Simulation:

- 1- open ADL
- 2- DC analysis → save dc operating point
- 3- Run

DC operating point from simulation:

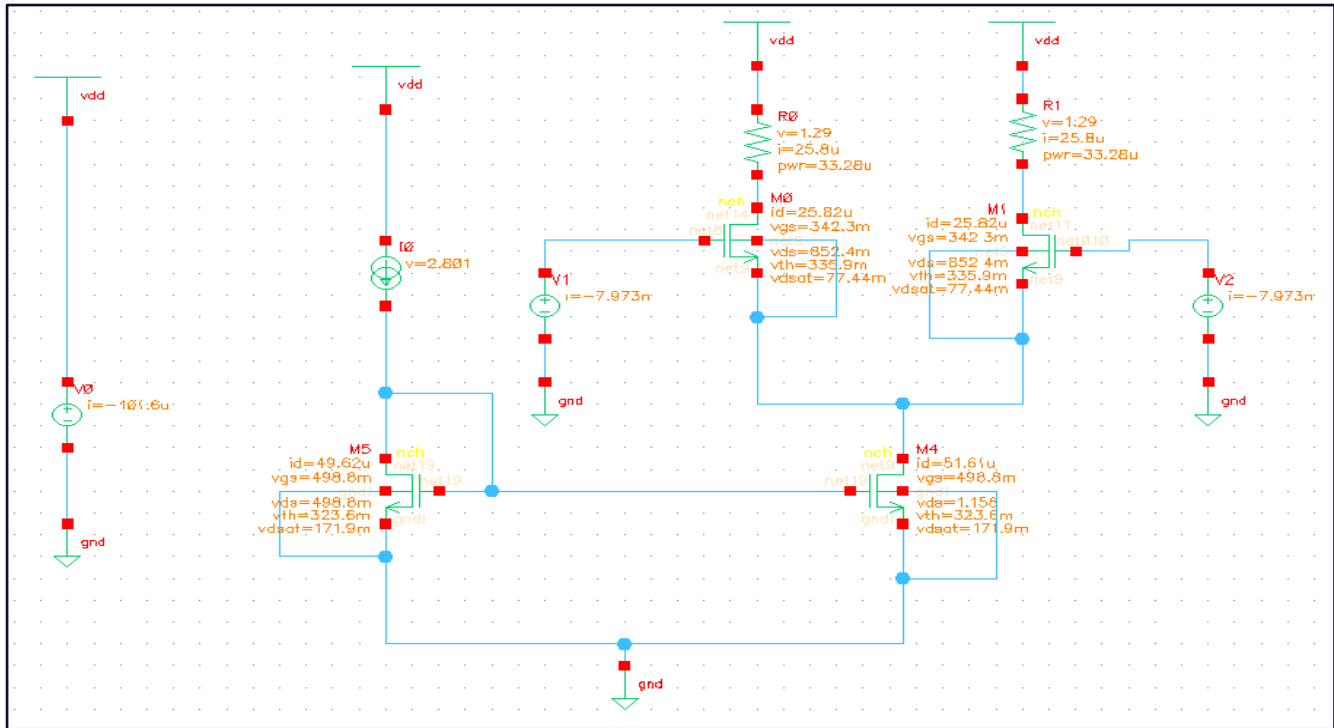


Figure 2: DC operating point from simulation

V _{DD}	V _{D5}	V _{G5}	V _{D4}	V _{G4}	V _{S1,2}	V _{D0,1}	V _{G0,1}	V _{S0,1}
3.3 V	498.8 mV	498.8 mV	1.158 V	498.8 mV	grounded	2.01 V	1.5 V	1.158 V

ii. Show the operating point of all transistors and make sure that they are in SAT (region 2)

Mosfet	Drain current		V _{GS}	V _{DS}	
	calculated	measured		calculated	measured
M ₀	25 μ A	25.8 μ A	342.3 mV	0.892 V	852.3 mV
M ₁	25 μ A	25.8 μ A	342.3 mV	0.892 V	852.3 mV
M ₄	50 μ A	51.61 μ A	498.8 mV	0.175 V	171.9 mV
M ₅	50 μ A	49.62 μ A	498.8 mV	—	498.8 mV

iii. Show the power consumption

Hand Analysis:

$$P = I^2 \times R$$

$$I = 25 \mu A, R = 50K \text{ ohm}$$

$$P = (25 \times 10^{-6})^2 \times 50 \times 10^3$$

$$P \text{ in } r1 = 3.125 \times 10^{-5} \text{ Watt}$$

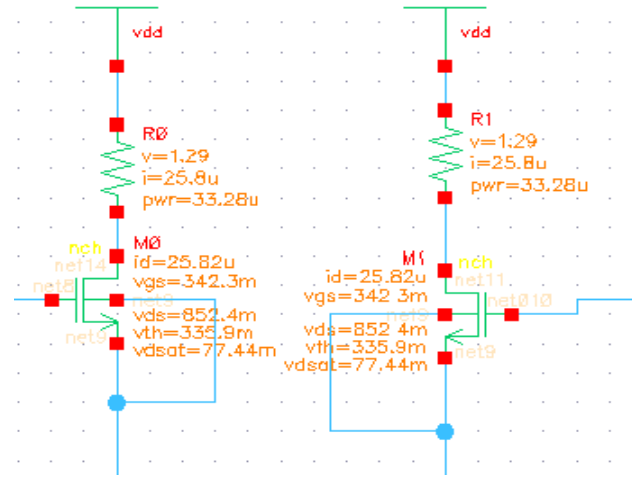
$$\text{total power} = 2 \times P \text{ in } r$$

$$P \text{ total} = 6.25 \times 10^{-5} \text{ Watt}$$

Simulation:

$$\text{power in simulation} = 33.28 \mu\text{Watt}$$

$$\text{total power} = 66.56 \mu\text{Watt}$$



Calculated Power dissipated in transistors :

In M_0, M_1 :

$$Power = I_{D1} \times V_{DS1} = 25 \times 10^{-6} \times 0.894 = 22.3 \mu\text{watt}$$

In M_4 :

$$Power = I_{D4} \times V_{DS4} = 50 \times 10^{-6} \times 1.158 = 57.9 \mu\text{watt}$$

In M_5 :

$$Power = I_{D5} \times V_{DS5} = 50 \times 10^{-6} \times 498.8 \times 10^{-3} = 24.94 \mu\text{watt}$$

Power dissipated in transistors from simulation:

In M_0, M_1 :

$$Power = I_D \times V_{DS} = 22 \mu\text{watt}$$

In M_4 :

$$Power = I_D \times V_{DS} = 59.76 \mu\text{watt}$$

In M_5 :

$$Power = I_D \times V_{DS} = 24.75 \mu\text{watt}$$

b. Run transient simulations (show the equation for every requirement ,how you get the results in cadence and the simulation setup)

Transient analysis:

- 1- open Adl.
- 2- analysis.
- 3- choose tran.
- 4- set certain output.

(APPLY INPUT TO M₂ 1 AMPLITUDE AND PHASE 0 AND , INPUT M₄ 1 AMPLITUDE AND 180 DEGREE PHASE)

i. Show the current of VOUT+ & VOUT- across time.

Equation in cadence calculator:	
IT(“/M1/D”)	$I_{out+} = \frac{V_{DD} - V_{out+}}{R_1}$

Output from simulation :Current of Vout+

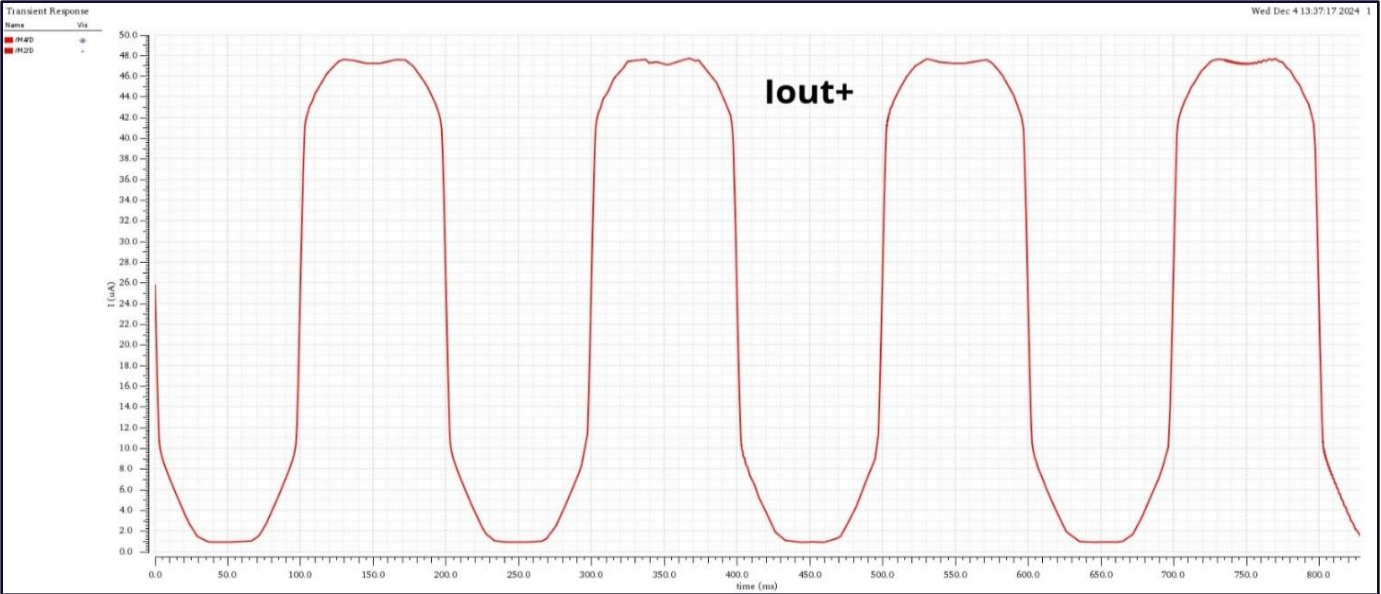


Figure 3: Output from simulation , Current of V_{out+}

Equation in cadence calculator:	
IT(“/M0/D”)	$I_{out-} = \frac{V_{DD} - V_{out-}}{R_0}$

Output from simulation :current of Vout-

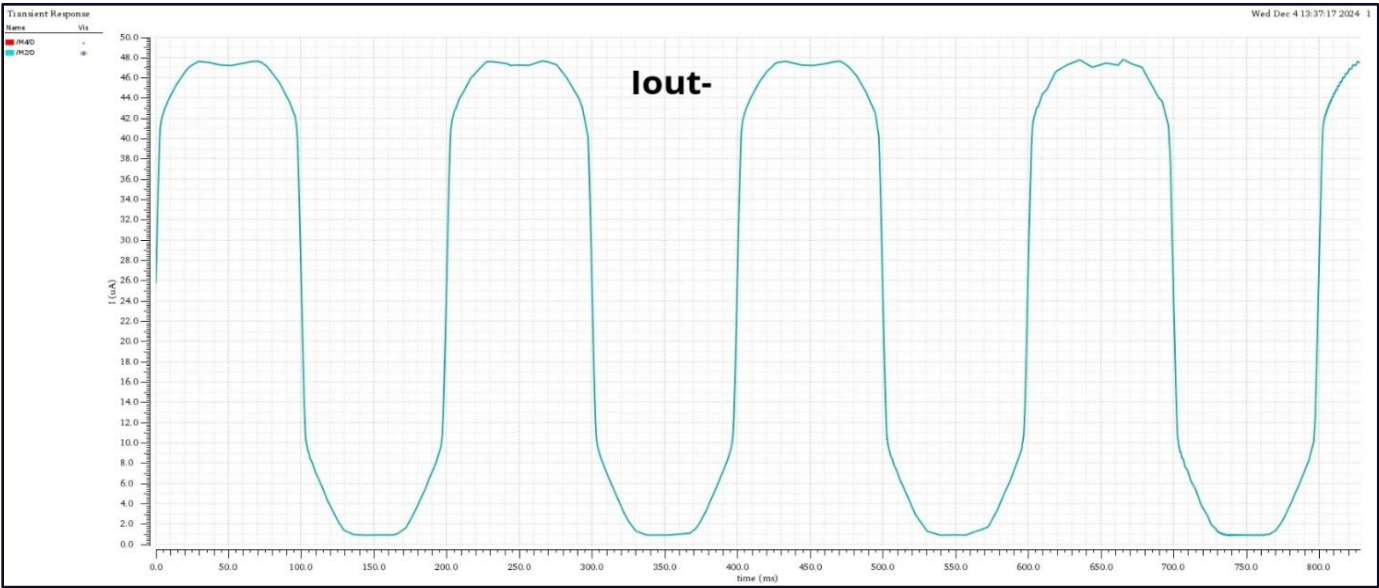


Figure 4: Output from simulation , Current of V_{out-}

ii. Show the voltage of V_{OUT+} & V_{OUT-} across time

Equations in cadence calculator: $VT("/Vout+")$ $VT("/Vout-")$	$V_{OUT+} = V_{CM} + \Delta v_{(-)}$ $V_{OUT-} = V_{CM} + \Delta v_{(+)}$
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Equation in cadence calculator: **VOLTAGE** V_{OUT+}

Output from simulation

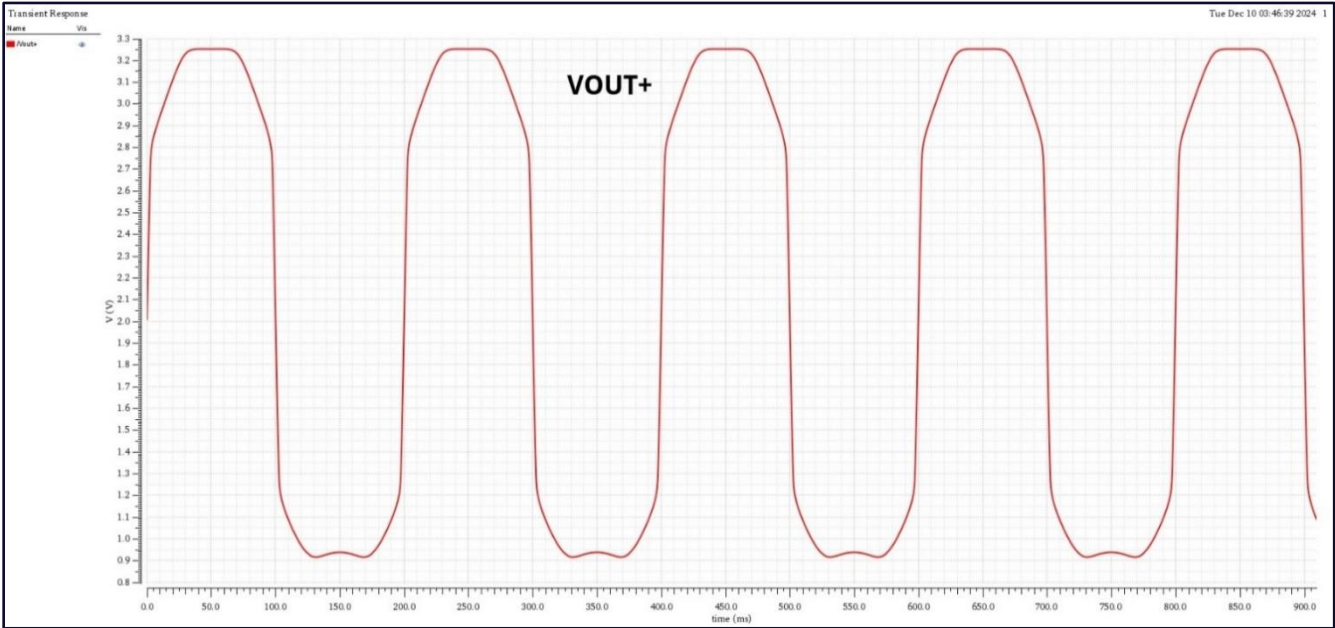


Figure 5: Output from simulation , Voltage of V_{out+}

Output from simulation **V_{OUT-}**

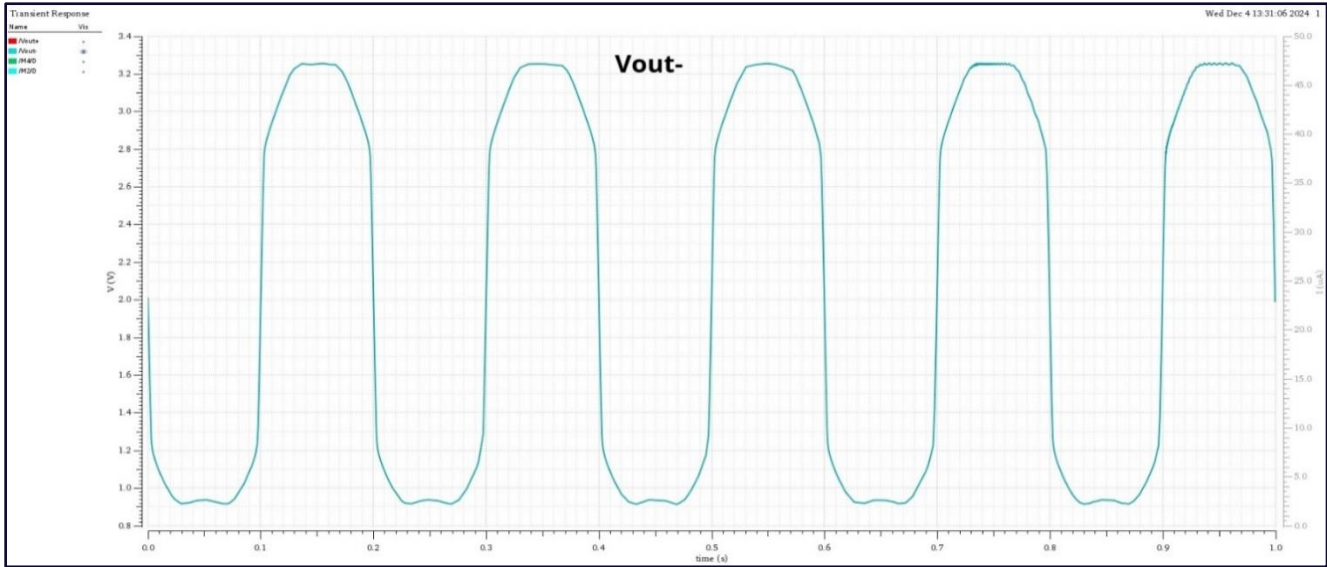


Figure 6: Output from simulation , Current of V_{out-}

iii. Show the voltage of V_{out} differential across time

Equations in cadence calculator: $VT("/Vout+") - VT("/Vout-")$	$V_{outdiff} = V_{out+} - V_{out-}$
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Output from simulation : **V_{outdiff}**

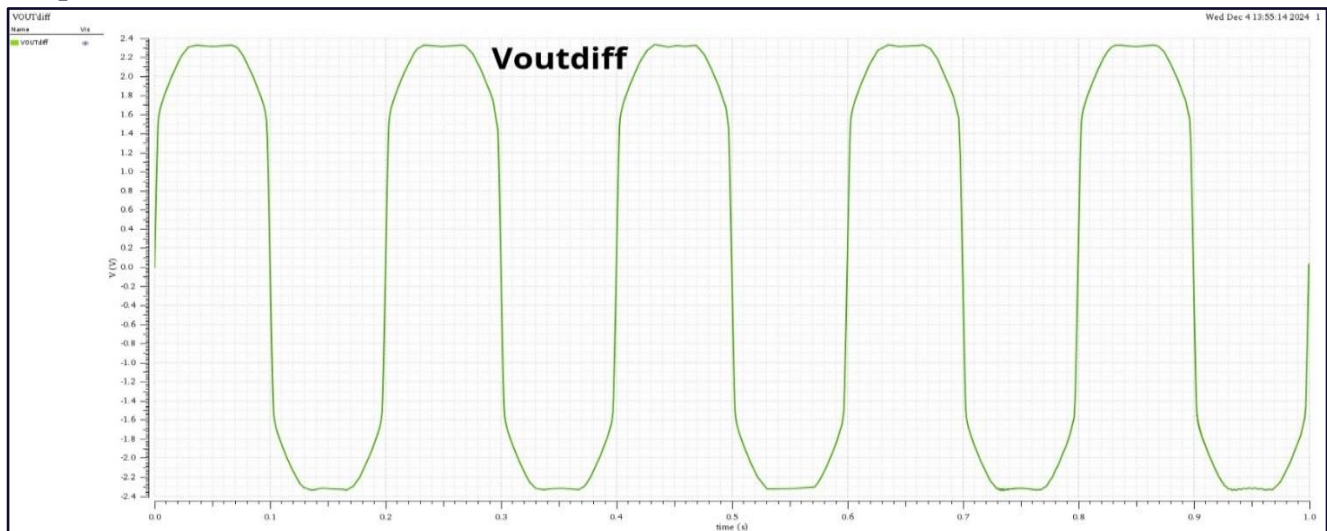


Figure 7: $V_{outdiff}$ from simulation

iv. Calculate the output swing

Equations in cadence calculator: $y_{max}(VT("/Vout+") - VT("/Vout-")) - y_{min}(VT("/Vout+") - VT("/Vout-"))$	OUTPUT SWING $= MAX\ PEAK(V_{outdiff}) - MIN\ PEAK(V_{outdiff})$ OUTPUT SWING = 4.679 V
---	---

Hand solution: Max Swing = $2 * (V_{cm_max} - V_{cm_min})$, $V_{cm_max} = V_{DD} = 3.3\ V$

$$V_{cm_min} = V_{cm} - V_{th} = 1.5 - 0.3359 = 1.164\ V$$

$$Max\ Swing = 2 * (3.3 - 1.16) = 4.3\ V$$

Output from simulation

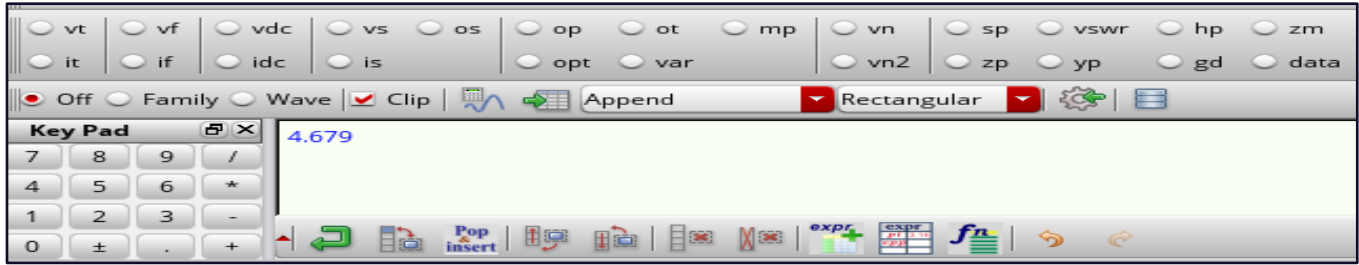


Figure 8: output swing from simulation

c. Run AC simulations (show equation for every requirement , how you get the results in cadence and the simulation setup)

Hand Analysis of this part are done by applying **half circuit concept**.

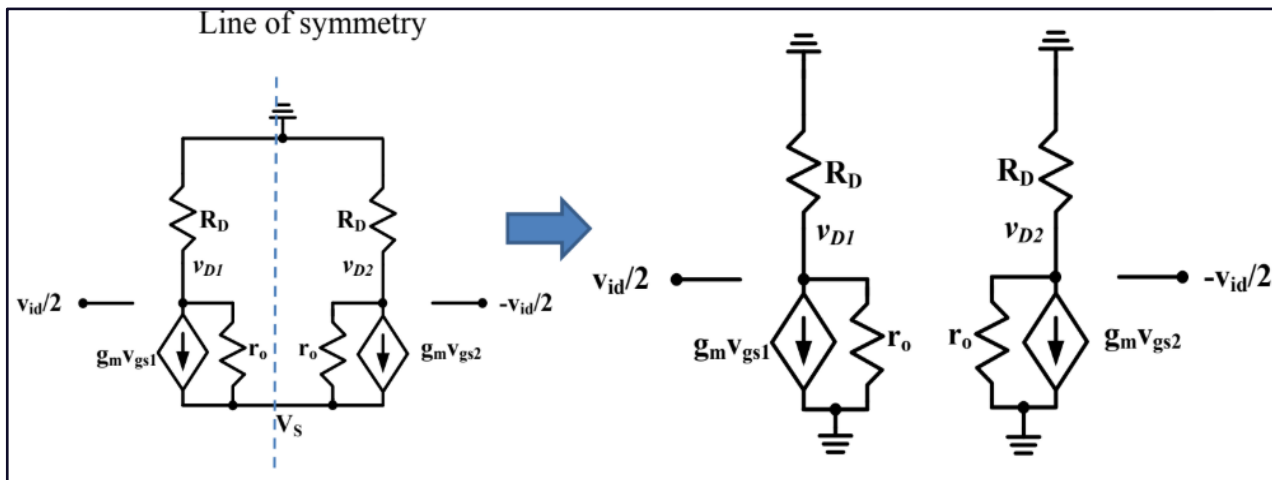


Figure 9: half circuit concept

Let

$$V_{d1} = V_{out-} \text{ \& } V_{d2} = V_{out+}$$

Values taken from simulation

$$g_m = 0.00046 \text{ A/V}$$

$$r_{o1} = 294.655 \text{ Kohm}$$

$$r_{os} = 722.482 \text{ Kohm}$$

By applying half circuit concept

$$V_{d1} = V_{out-} = g_m * (R_D \parallel r_{o1}) * \frac{v_{id}}{2} = 9.83 \text{ volt}$$

$$V_{d2} = V_{out+} = g_m * (R_D \parallel r_{o1}) * \frac{-v_{id}}{2} = -9.83 \text{ volt}$$

By adding the source resistance in consideration so it converted to 2 common source amplifiers with source resistance degeneration but because of odd symmetry $V_S = 0$ a virtual ground in parallel with R_{SS} so it will be cancelled so

$$A_{\text{diff-diff}} = \frac{V_{\text{out-}} - V_{\text{out+}}}{v_{id}} = \frac{9.83 - (-9.83)}{1} = 19.66$$

$$A_{\text{diff-CM}} = \frac{\frac{V_{\text{out-}} + V_{\text{out+}}}{2}}{v_{id}} = \frac{-g_m(R_D \parallel r_{o1}) + g_m(R_D \parallel r_{o1})}{2 * 1} = 0$$

The same in the case of the Common mode input voltage signal but here is an even symmetry and V_S not equal zero so R_{SS} will be taken in consideration

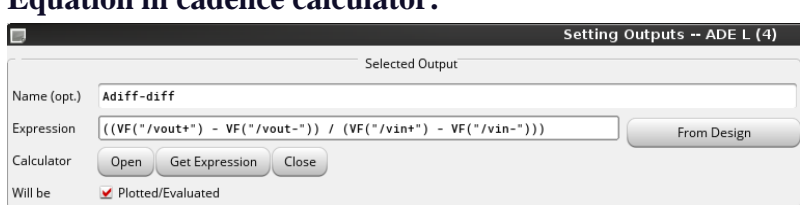
$$R_{SS} = r_{os} = 722.482 \text{ Kohm}$$

$$V_{d1} = V_{d2} = V_{\text{out-}} = V_{\text{out+}} = \frac{g_m(R_D \parallel r_{o1})}{1 + 2g_m R_{SS}} * V_{CM} = 0.0298 \text{ volts}$$

$$A_{\text{CM-diff}} = \frac{V_{\text{out-}} - V_{\text{out+}}}{v_{CM}} = \frac{g_m(R_D \parallel r_{o1})}{1 + 2g_m R_{SS}} - \frac{g_m(R_D \parallel r_{o1})}{1 + 2g_m R_{SS}} = 0$$

$$A_{\text{CM-CM}} = \frac{\frac{V_{\text{out-}} + V_{\text{out+}}}{2}}{v_{CM}} = \frac{V_{\text{out+}}}{1} = 29.8 \text{ m}$$

1-Get $A_{\text{diff-diff}}$

Equation in cadence calculator:	
	$A_{\text{diff-diff}} = \frac{V_{\text{out+}} - V_{\text{out-}}}{V_{\text{in+}} - V_{\text{in-}}} = 19.64$

Output from simulation:

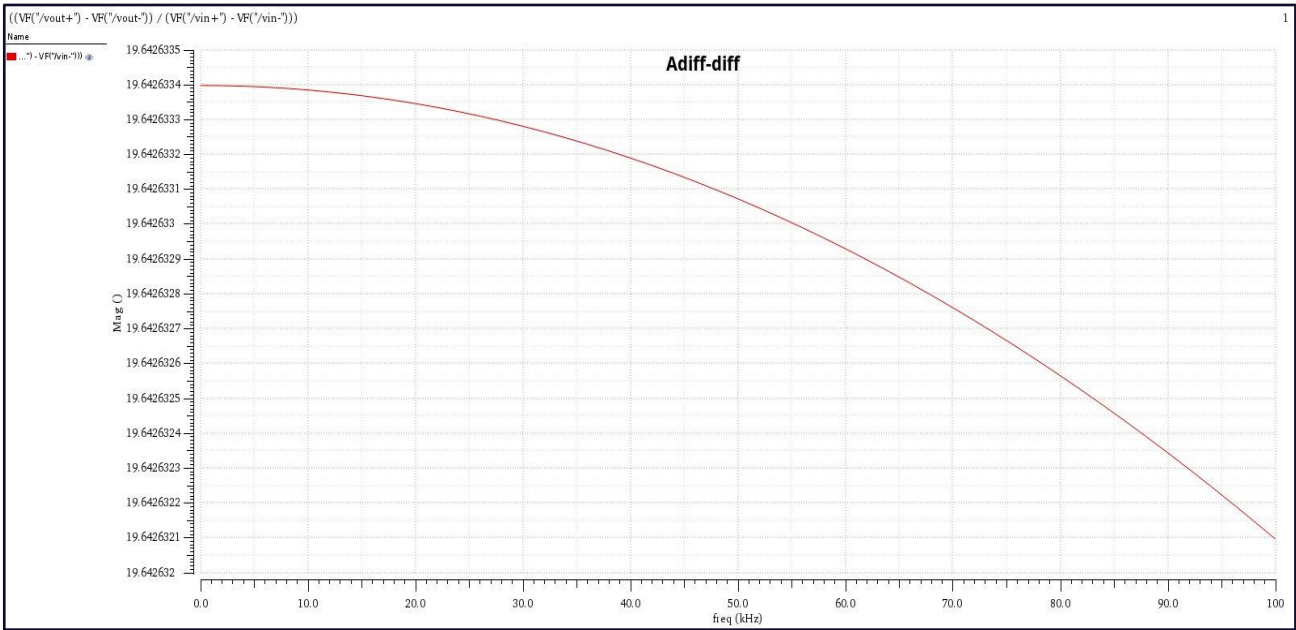


Figure 10: $A_{diff-diff}$ from simulation

2- Get $A_{diff-CM}$

Equation in cadence calculator:

Setting Outputs -- ADE L (4)

Selected Output

Name (opt.)

Expression

Calculator

Will be ☒ Plotted/Evaluated

$$A_{diff-CM} = \frac{V_{out+} + V_{out-}}{2 \cdot (V_{in+} - V_{in-})} = 0$$

Output from simulation:

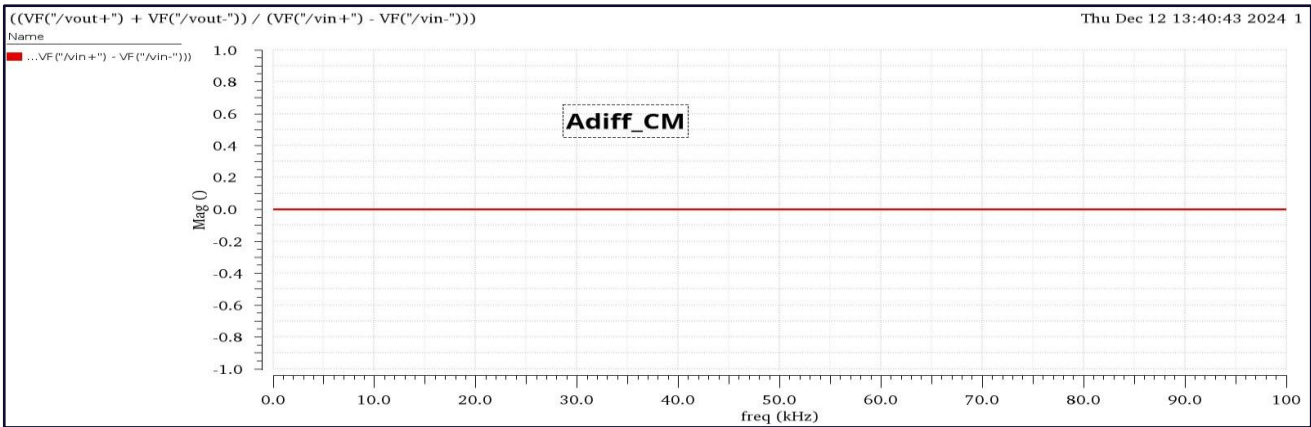


Figure 11: $A_{diff-CM}$ from simulation

3-Get A_{CM-CM}

Equation in cadence calculator:

Setting Outputs -- ADE L (2)

Selected Output

Name (opt.)

ACM_CM

Expression

$$\frac{(VF("/Vo+")) + VF("/Vo-"))}{(VF("/Vo+")) + VF("/Vo-"))}$$

Calculator

Open

Get Expression

Close

Will be

☒ Plotted/Evaluated

From Design

$$A_{CM-CM} = \frac{V_{out1} + V_{out2}}{V_{in1} - V_{in2}} = 34.36m$$

Output from simulation

The figure shows a Bode plot for the ACM-CM output. The x-axis represents frequency in kHz, ranging from 0.0 to 100.0. The y-axis represents the magnitude in dB, ranging from 34.36905 to 34.36927. A red curve shows the magnitude increasing with frequency. A label 'ACM-CM' is placed on the curve at approximately 80 kHz.

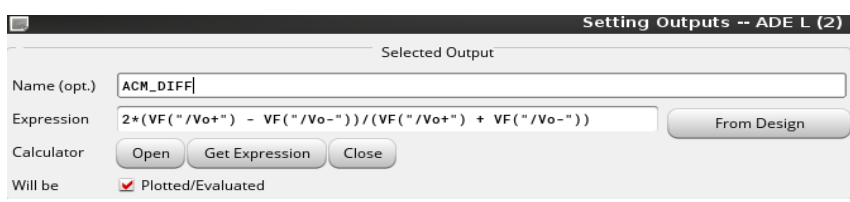
freq (kHz)	Mag (m)
0.0	34.36905
10.0	34.36906
20.0	34.36907
30.0	34.36908
40.0	34.36909
50.0	34.36910
60.0	34.36911
70.0	34.36912
80.0	34.36913
90.0	34.36914
100.0	34.36915

Figure 12: A_{CM-CM} from simulation

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4. Get $A_{CM-diff}$.

Equation in cadence calculator:



The screenshot shows the 'Setting Outputs -- ADE L (2)' window. The 'Name (opt.)' field contains 'ACM_DIFF'. The 'Expression' field contains the formula: $2 * (VF('Vo+') - VF('Vo-')) / (VF('Vo+') + VF('Vo-'))$. The 'Calculator' section has buttons for 'Open', 'Get Expression', and 'Close'. The 'Will be' section has a checked box for 'Plotted/Evaluated'.

$$A_{CM-diff} = \frac{V_{out1} - V_{out2}}{V_{in1} + V_{in2}} = 0$$

Output from simulation:

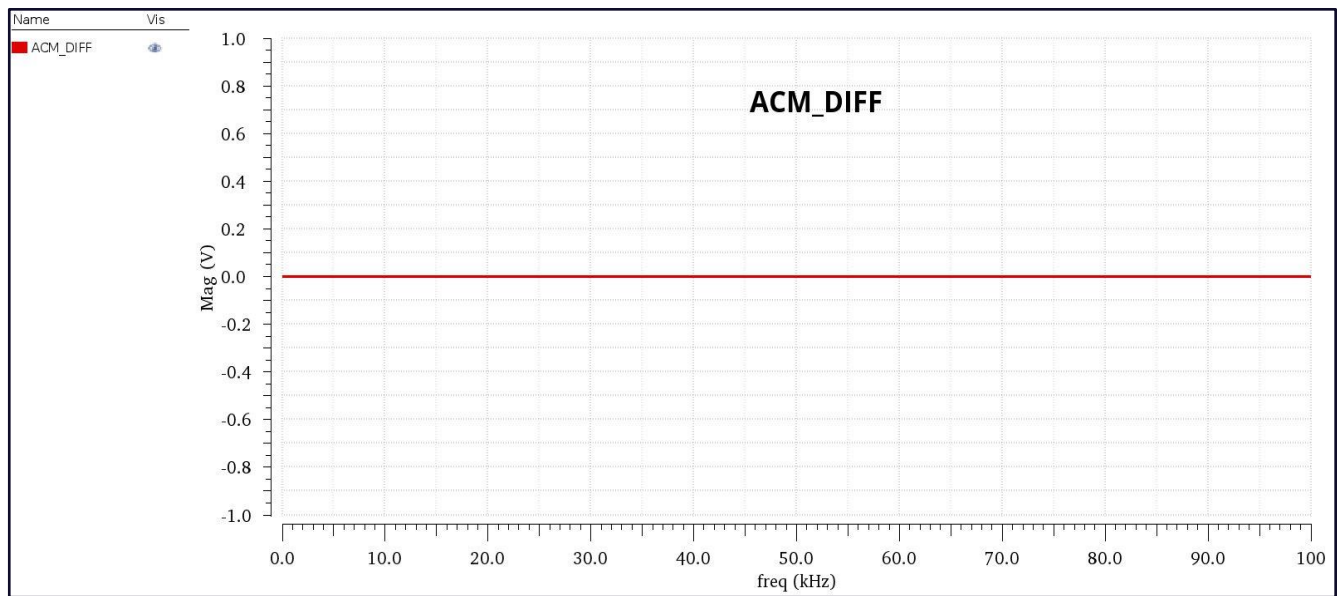


Figure 13: $A_{CM-diff}$ from simulation

5-CMRR

$$CMRR = \frac{A_{diff_diff}}{A_{cm_diff}} \approx \infty$$

6- $R_{out-diff}$:

Equation in cadence calculator:

$$R_{out-diff} = \frac{V_{out-diff}}{I_{out-diff}} = 85.43k\Omega$$

- Output resistance (R_{out}) is defined as:

$$R_{out-diff} = (V_{out-diff})/(I_{out-diff}) = 85.43k\Omega$$
- $V_{out-diff}$ is the differential-mode output voltage, which in this case is approximated by $VF("/net15") - VF("/net14")$ (the voltage difference across the two outputs).
- I_{out_CM} is the differential-mode output current, which flows through the DC source $V5$, represented by $IF("/V5/PLUS")$.
- We used the following expression in the Cadence Calculator:

$$(VF("/net15") - VF("/net14"))/(IF("/V5/PLUS"))$$

- Here's what each term represents:
 - $VF("/net15")$: $+V_{out}$
 - $VF("/net14")$: $-V_{out}$
 - $IF("/V5/PLUS")$: The current flowing through the DC voltage source $V5(V_{out})$.
- The expression calculates the ratio of the voltage difference across the two output nodes to the current through the DC source, **differential output resistance $R_{out-diff}$** .

Output from simulation:

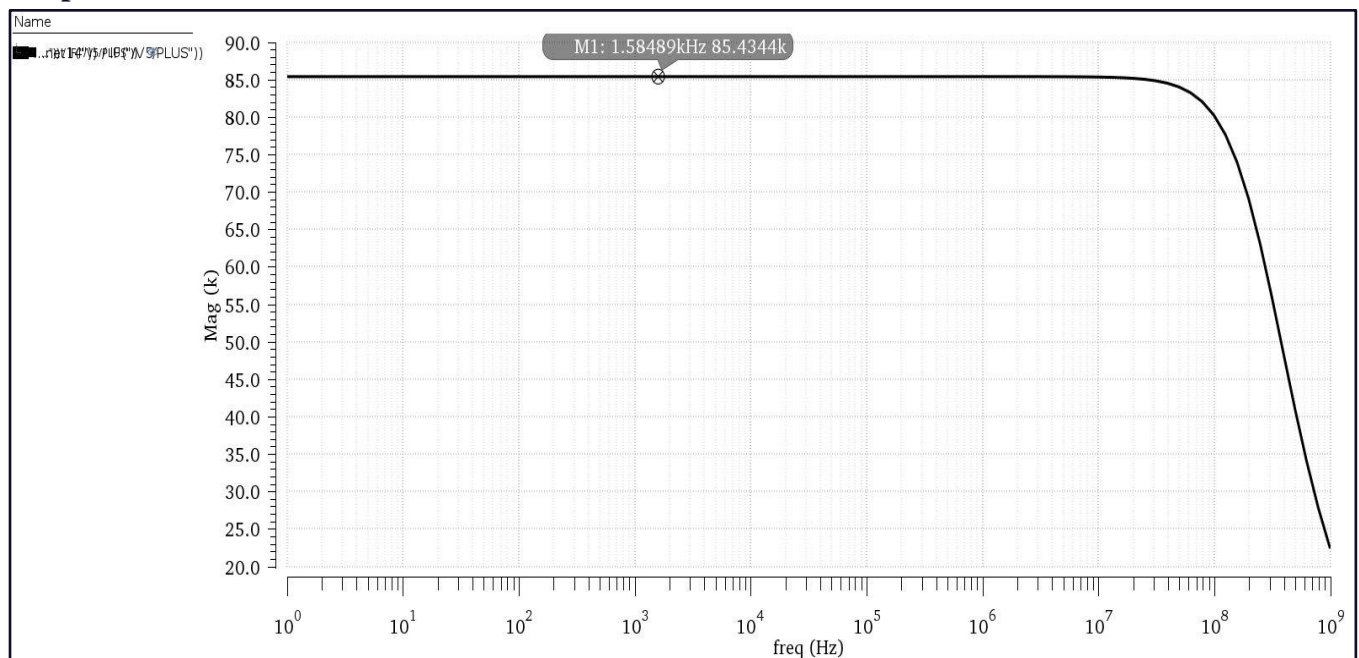
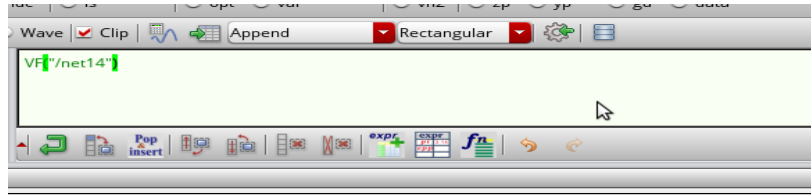


Figure 14: $R_{out-diff}$ from simulation

7- R_{out-CM}

Equation in cadence calculator:



$$R_{out-CM} = \frac{V_{out-CM}}{I_{out-CM}} \approx \frac{R_1}{2} = 24.9699 k\Omega$$

$$R_{out-CM} = 24.9699 k\Omega$$

- Output resistance (R_{out}) is defined as:

$$R_{out-CM} = \frac{V_{out-CM}}{I_{out-CM}}$$

- Since the AC magnitude of the current source is 1 A, the voltage at the output node (V_{out}) is numerically equal to (R_{out}) directly:

$$R_{out-CM} = V_{out-CM}$$

Note: $VF("/net14") = V_{out}$

- We used $VF("/net14")$, which calculates the voltage at the output node net14
- 1. Because the AC current source is set to 1 A, $VF("/net14")$ directly gives the small-signal **common-mode resistance** R_{out-CM} .
- The plot shows how R_{out-CM} behaves across frequencies, starting flat at low frequencies (~25 k Ω) and decreasing at higher frequencies due to parasitic effects.

Output from simulation:

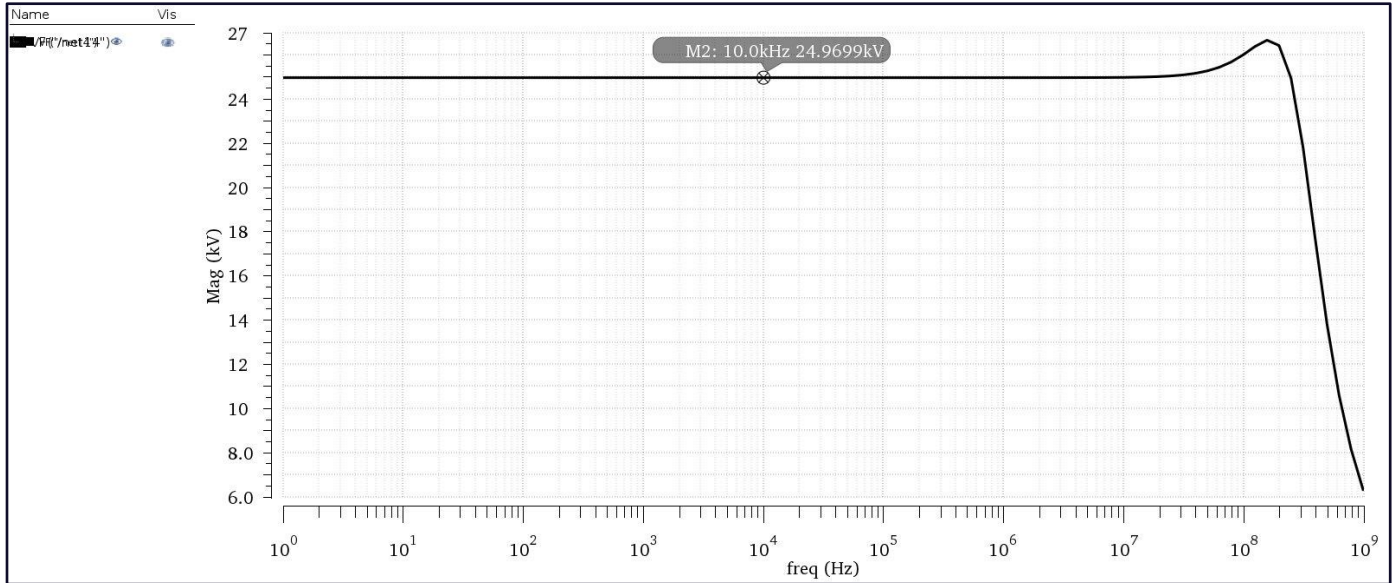


Figure 15: R_{out-CM} from simulation

Problem2 Current mirror.

Simulator Circuit:

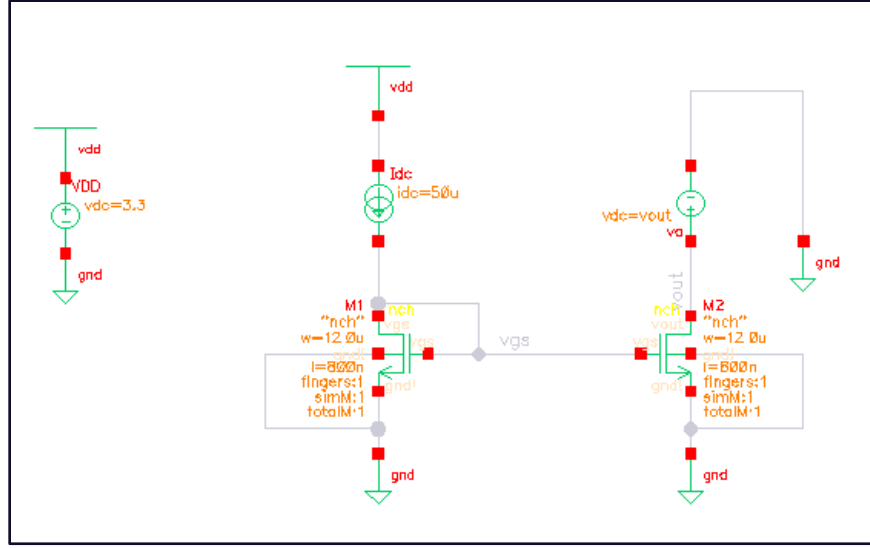


Figure 16: Problem 2 circuit

Part1

Hand analysis:

As D_1 & G_1 are connected so Q_1 will be
In saturation

$$I_{D1} = 0.5 * K_n * (V_{GS1} - V_T)$$

$$V_{GS1} = V_{DS1} = 0.4187 V$$

$$V_{DSAT} = V_{GS1} - V_T = 0.4187 - 0.3397 = 0.079 V$$

$$V_{GS1} = V_{GS2}$$

From the concept of current mirroring
Neglecting channel length modulation

$$\frac{I_{OUT}}{I_{REF}} = \frac{\frac{W1}{L1}}{\frac{W2}{L2}} = 1, \text{ SO } I_{OUT} = I_{REF} = I_{DC} = 50 \mu\text{Amp}$$

$$V_{DS2} = V_{OUT} = 2.6 V$$

As $V_{GS2} > V_T$ And $V_{DS2} > V_{GS2} - V_T$ Q_2 is in saturation

As $V_{GS1} = V_{GS2}$ And $V_{T1} = V_{T2}$

$$V_{DSAT1} = V_{DSAT2} = 0.079 V$$

$$\text{Relative Current Error} = \frac{I_{OUT} - I_{REF}}{I_{REF}} \times 100$$

From hand analysis:

$$\textbf{Relative Current Error} = 0$$

From simulation:

$$\textbf{V}_{GS1} = \textbf{V}_{DS1} = \textbf{V}_{GS2} = \textbf{0.4187}$$

$$\textbf{V}_{DSAT1} = \textbf{V}_{DSAT2} = \textbf{0.1187 V}$$

$$\textbf{V}_{DS2} = \textbf{2.6 V}$$

$$\textbf{I}_{OUT} = \textbf{59.69 uA}$$

$$\textbf{I}_{REF} = \textbf{50.2 uA}$$

$$\textbf{Relative Current Error} = \frac{59.69 - 50.2}{50.2} \times 100 = \textbf{18.9\%}$$

Part2

1)

Output from simulation:

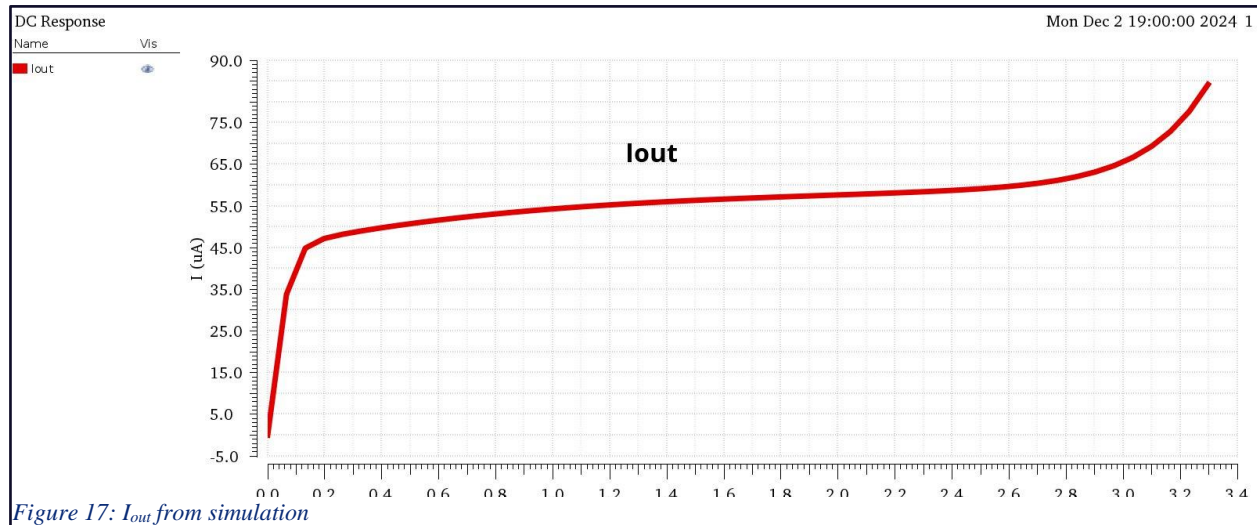


Figure 17: I_{out} from simulation

Observation:

Slight increasing in output voltage (V_{out}) will set Q_2 initially in triode region such as the transistor reacts as a resistor so output current (I_{out}) has a linear relation with output voltage (I_{out})), then after a specific voltage known as overdrive voltage Q_2 gets in saturation such as current is kept constant while increasing voltage but as a result of channel length modulation there is a small increase in output current, And with the increase of the output voltage the transistor fall in break down region in which it lose its characteristics.

2)

Output from simulation:

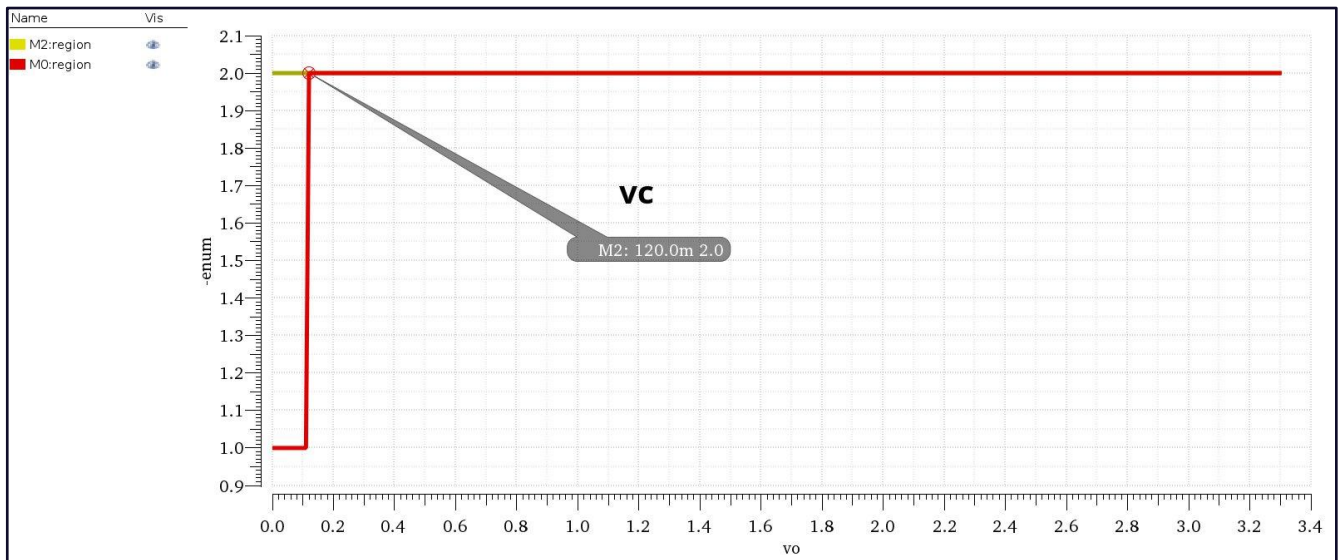


Figure 18: V_c from simulation

Comments:

Compliance voltage from its definition is the minimum voltage to derive the current mirror in a right way which gives approximately a constant current.

From simulation we found that

$$\text{compliance voltage} = 120\text{m V}$$

, after this value the transistor Q_2 will be in saturation and work as ideal current mirror

3)

The overdrive voltage is the minimum voltage that makes Q_2 saturation.

We neglect Q_1 as its drain and gate are connected so any small voltage will set it in saturation.

Which calculated before from part1

$$V_{DSAT} \text{ from dc operating point} = 118\text{ mV}$$

4)

Output from simulation:

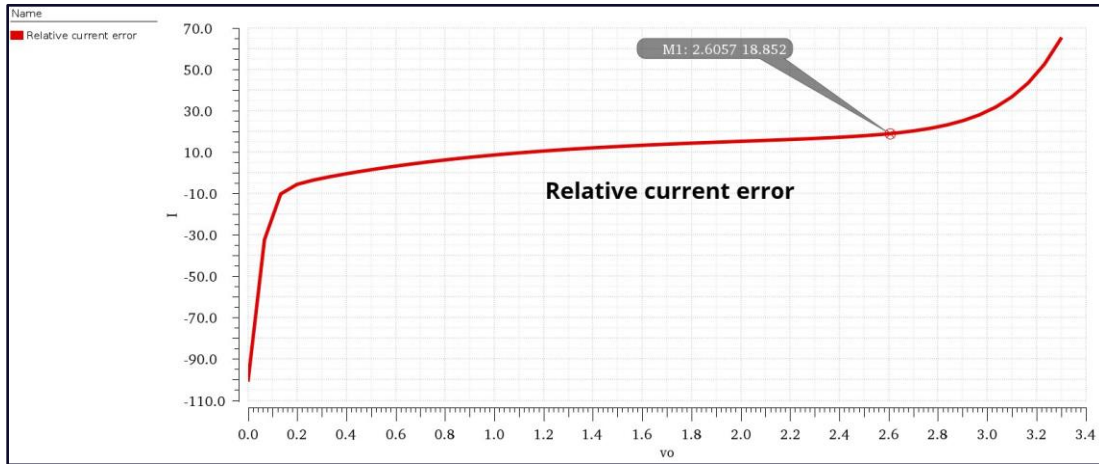


Figure 19: relative current error

$$\text{Relative Current Error} = \frac{I_{OUT} - I_{REF}}{I_{REF}} * 100 = \left(\frac{I_{OUT}}{I_{REF}} - 1 \right) * 100$$

So, it has the Same variation as I_{OUT} , but with a different slope and shifted.

5)

Output from simulation:

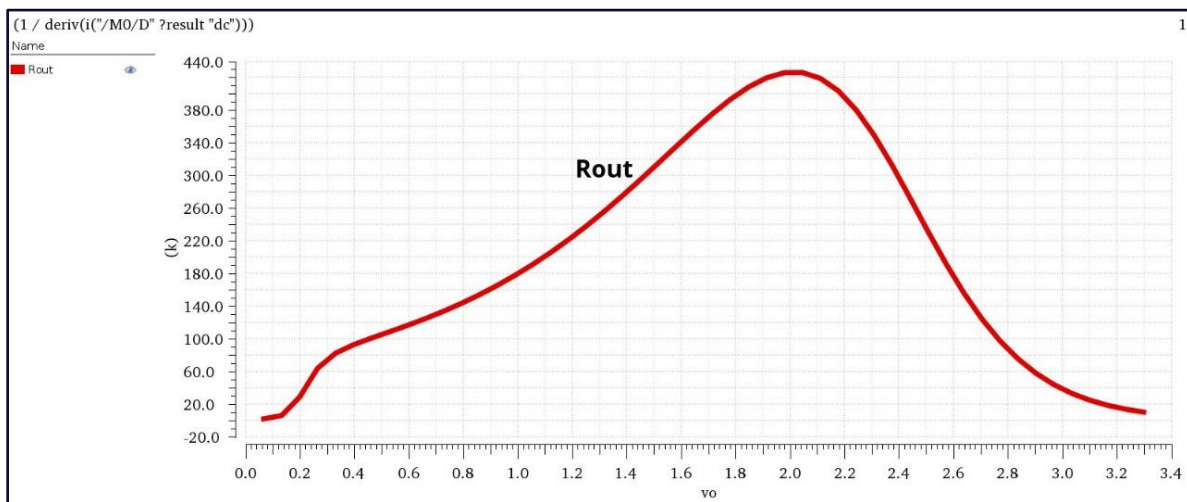


Figure 20: R_{out} from simulation

Comment:

At low V_{ov} values, R_{out} starts low and increases steadily. This could correspond to the saturation of the transistor or the mirror's inability to sustain higher resistance at low output, R_{out} a maximum value at an intermediate V_{ov} , indicating optimal operation of the current mirror at this point. This is where the circuit might achieve the highest output impedance, After the peak, R_{out} begins to drop with further increases in V_{ov} . This suggests the circuit enters a region where it can no longer maintain a high impedance, likely due to the transistor moving out of its active region.

Output from simulation:

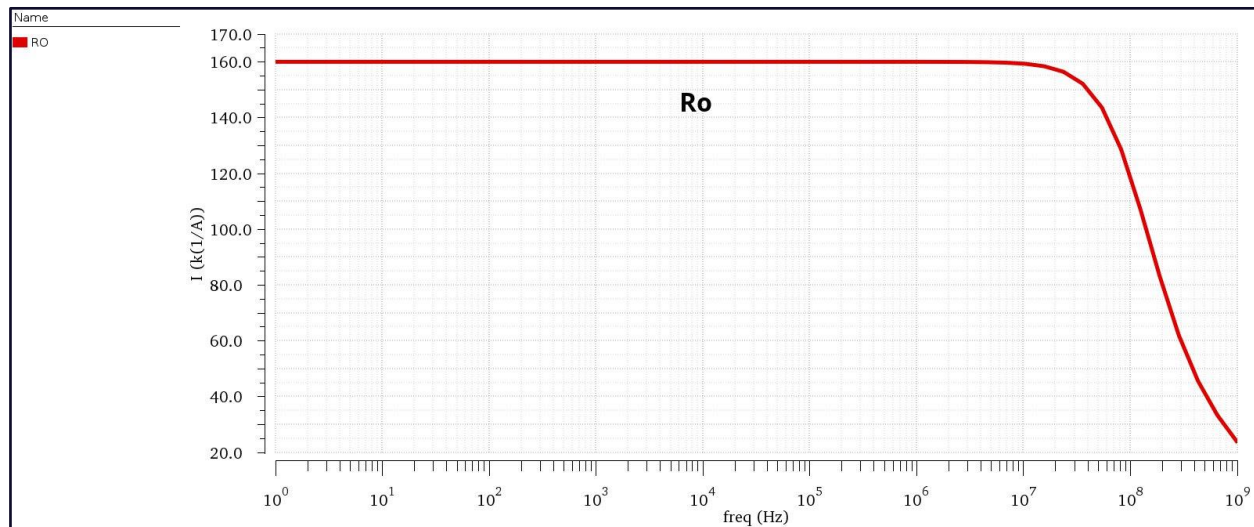


Figure 21: R_o from simulation

At $V_{out} = 2.6 V$

$R_{out} = 160 K\Omega$

We perform a frequency sweep of R_{out} to identify the frequency at which the influence of the internal capacitance of the transistor becomes significant. This analysis highlights the point where the capacitive effects begin to dominate, impacting the impedance and altering the circuit's performance.

Part3

1- Plot output current vs L :

Output from simulation:

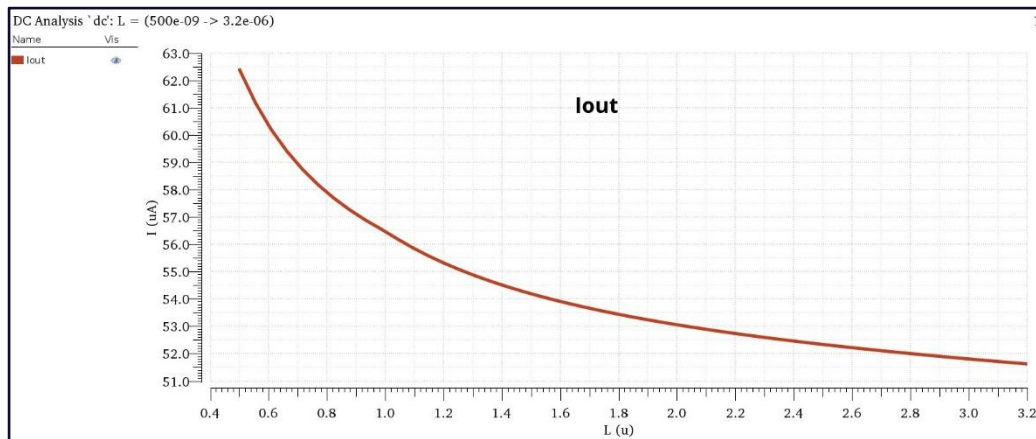


Figure 22: output current vs L

Comment on the results:

$$\frac{I_{OUT}}{I_{REF}} = \frac{\frac{W1}{L1} (1 + \lambda V_{ds2})}{\frac{W1}{L1} (1 + \lambda V_{ds1})}, \quad \lambda \text{ is in an inverse relation with } L$$

$$V_{ds2} = 2.1 \text{ V} \& V_{ds1} = 0.4 \text{ V}$$

So, if we neglected V_{ds1} as it too small compared to V_{ds2} we get that the inverse relation between L and I_{OUT} , as I_{OUT} direct proportional to λ and as L increases, λ decreases. And because it is not an exact linear relation the decreasing in the graph is a curve.

Note that the variation in **L** is the same so λ is the same in the 2 transistors.

2- Use calculator to get relative error :

Output from simulation:

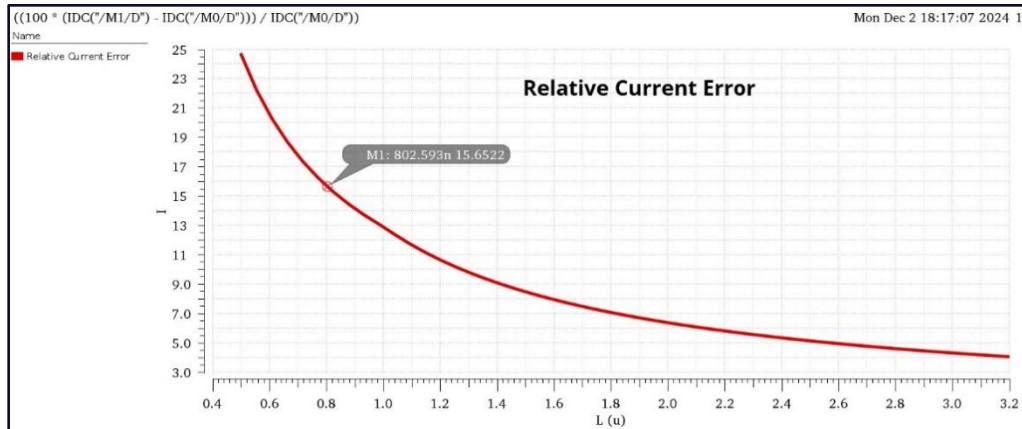


Figure 23: relative error from simulation

Comment:

As L increases the channel length modulation effect decreases so that ,the relative current error decreases as it is easy to know where it could be neglected, And the output current only depends on the input current and there dimensions (**W & L**) .